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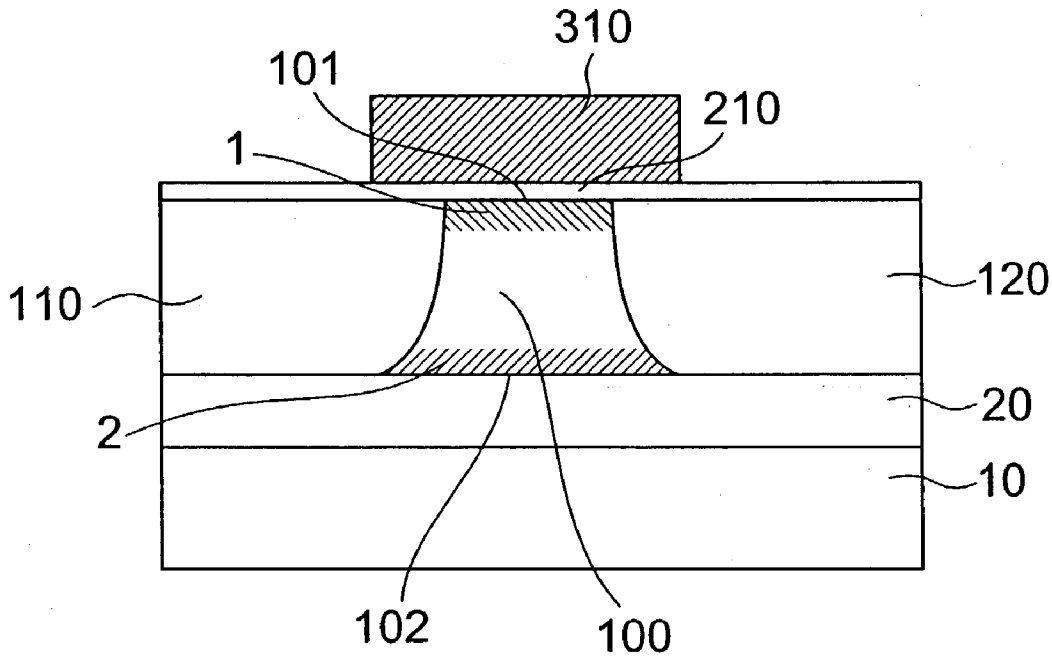


FIG. 1

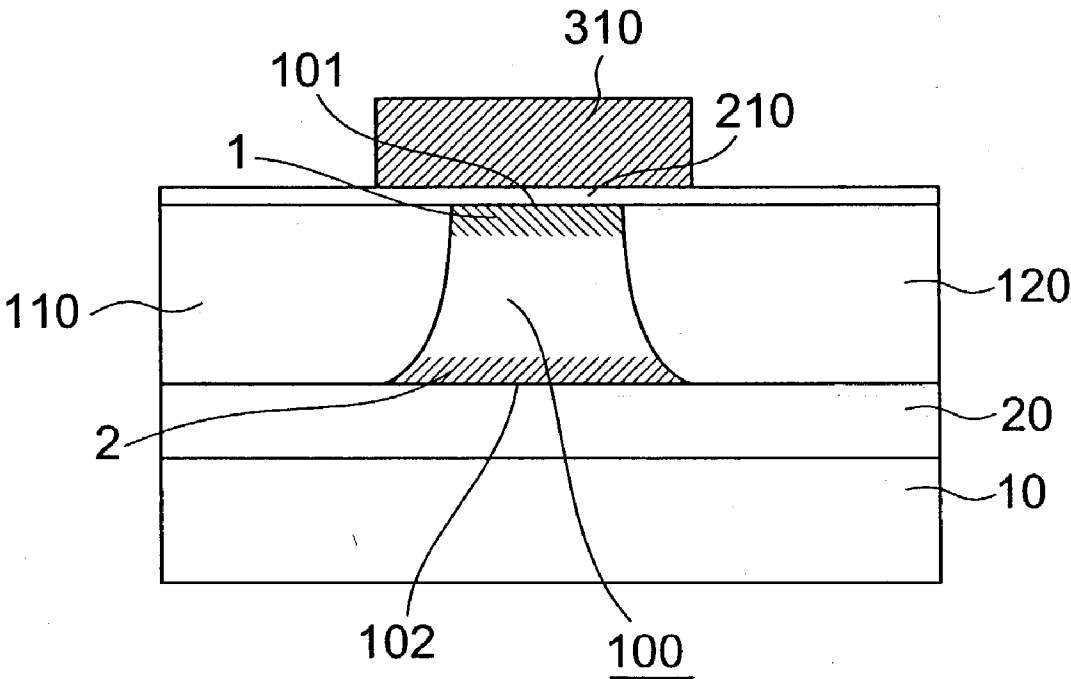


FIG. 2A

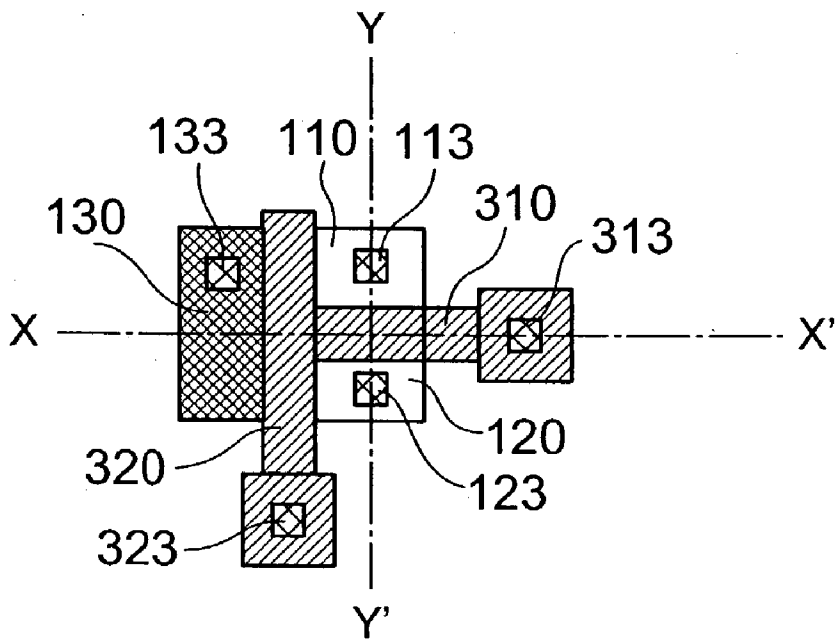


FIG. 2B

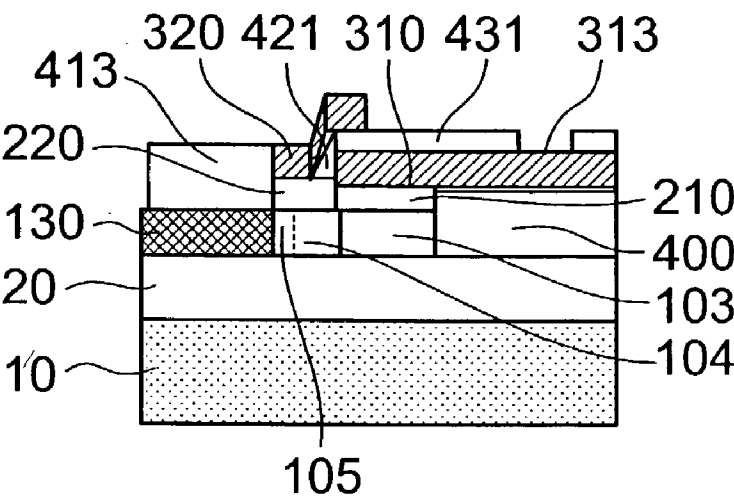


FIG. 3

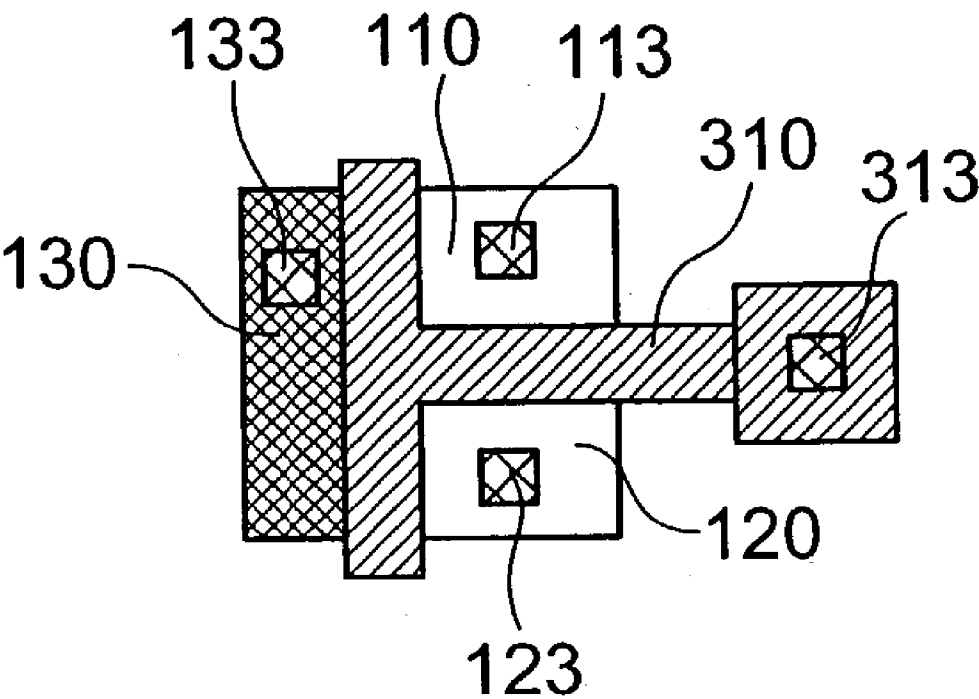


FIG. 4A

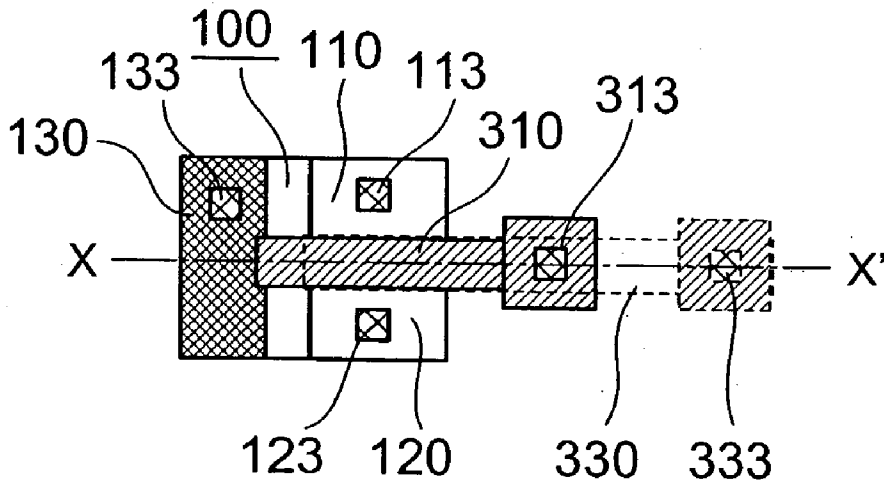


FIG. 4B

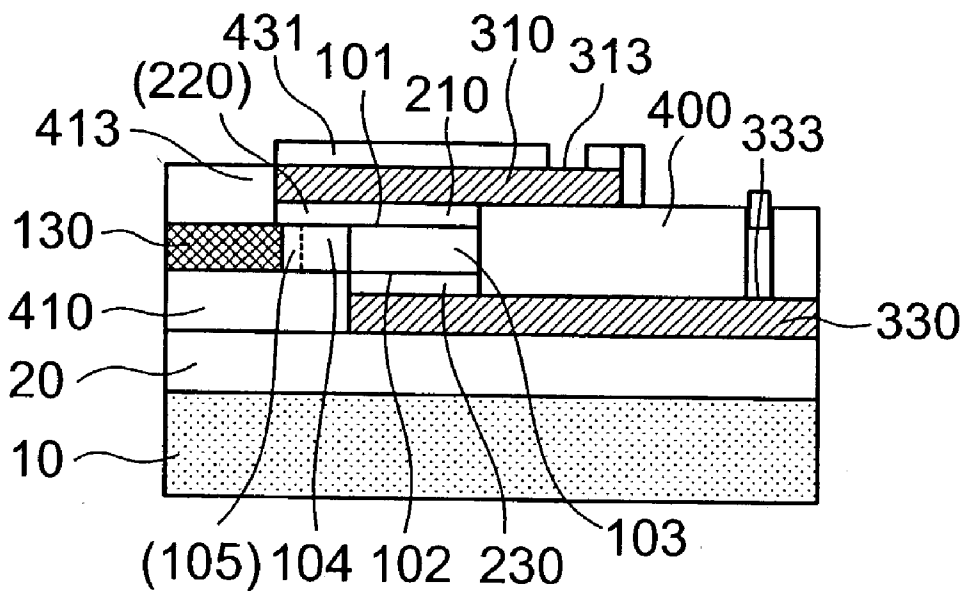


FIG. 5A

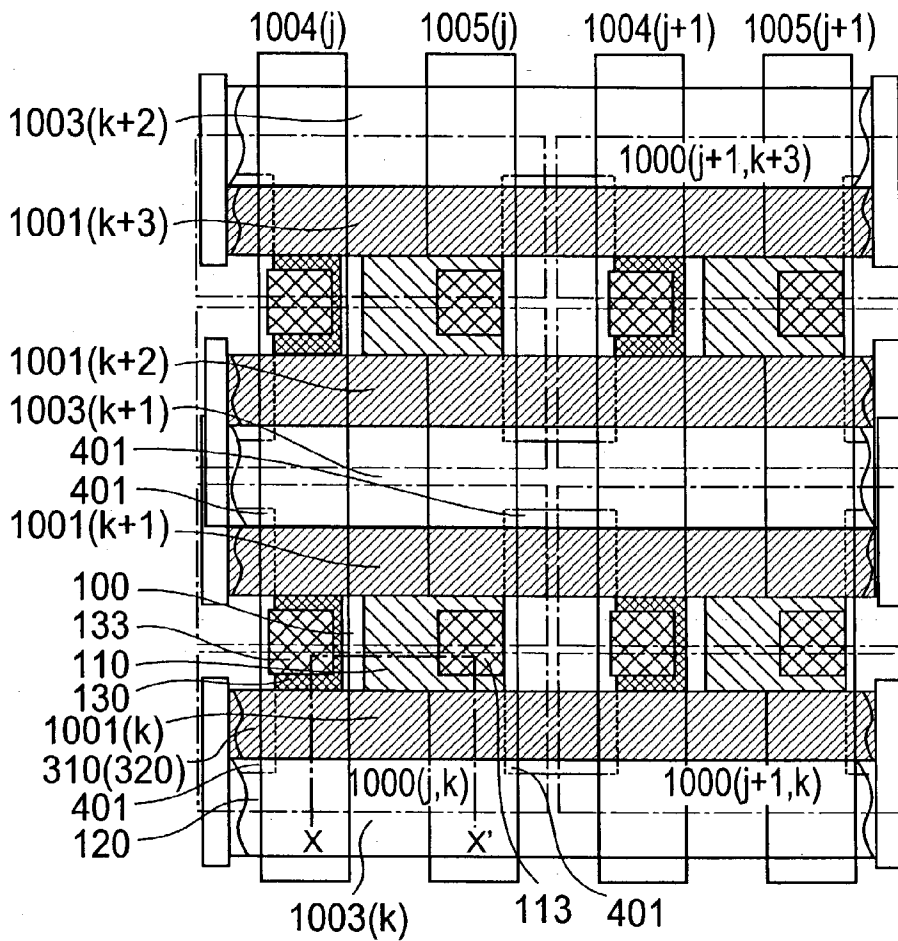


FIG. 5B

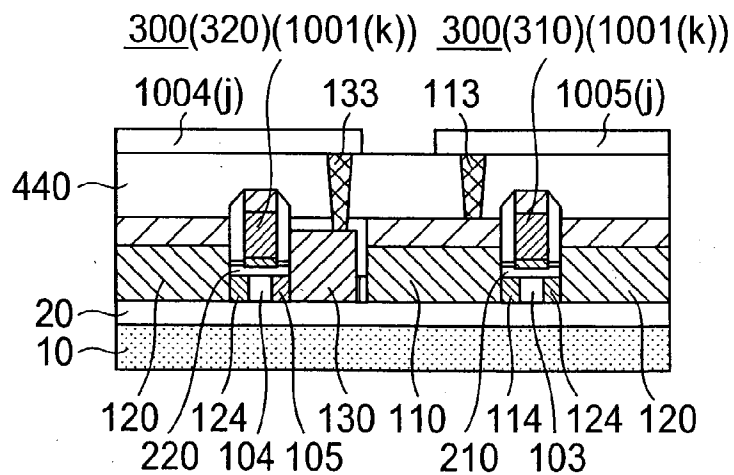


FIG. 6A

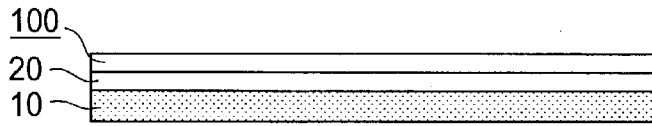


FIG. 6B

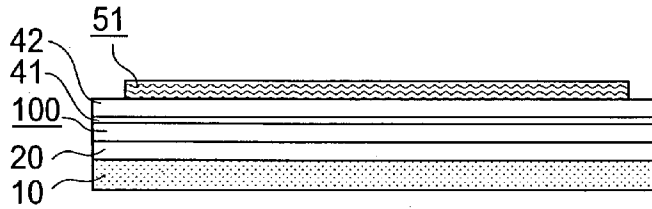


FIG. 6C

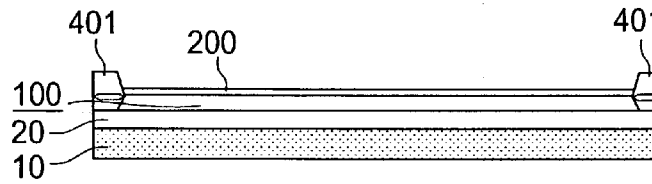


FIG. 6D

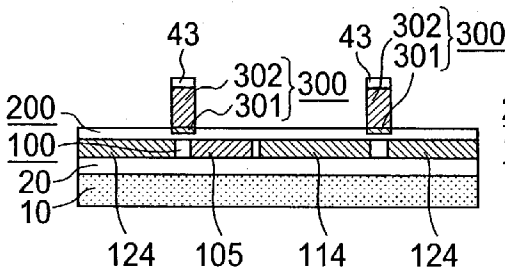


FIG. 6E

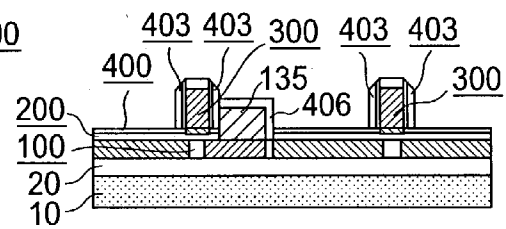


FIG. 6F

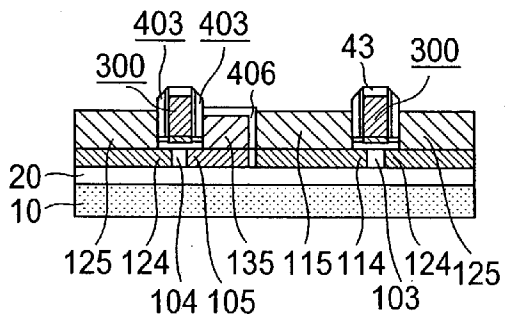


FIG. 6G

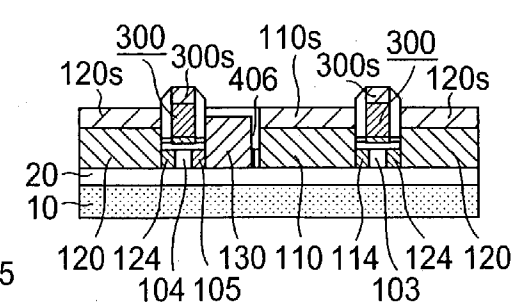


FIG. 7

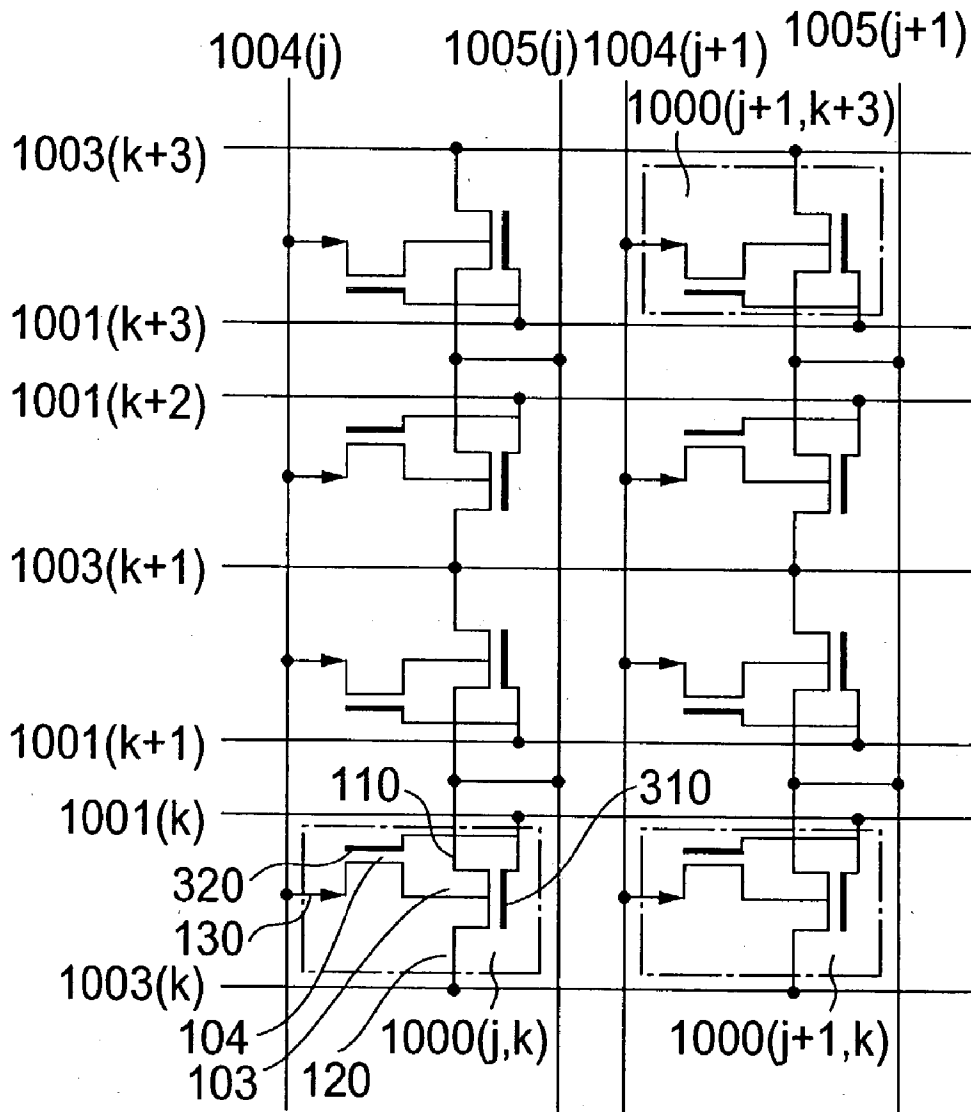


FIG. 8

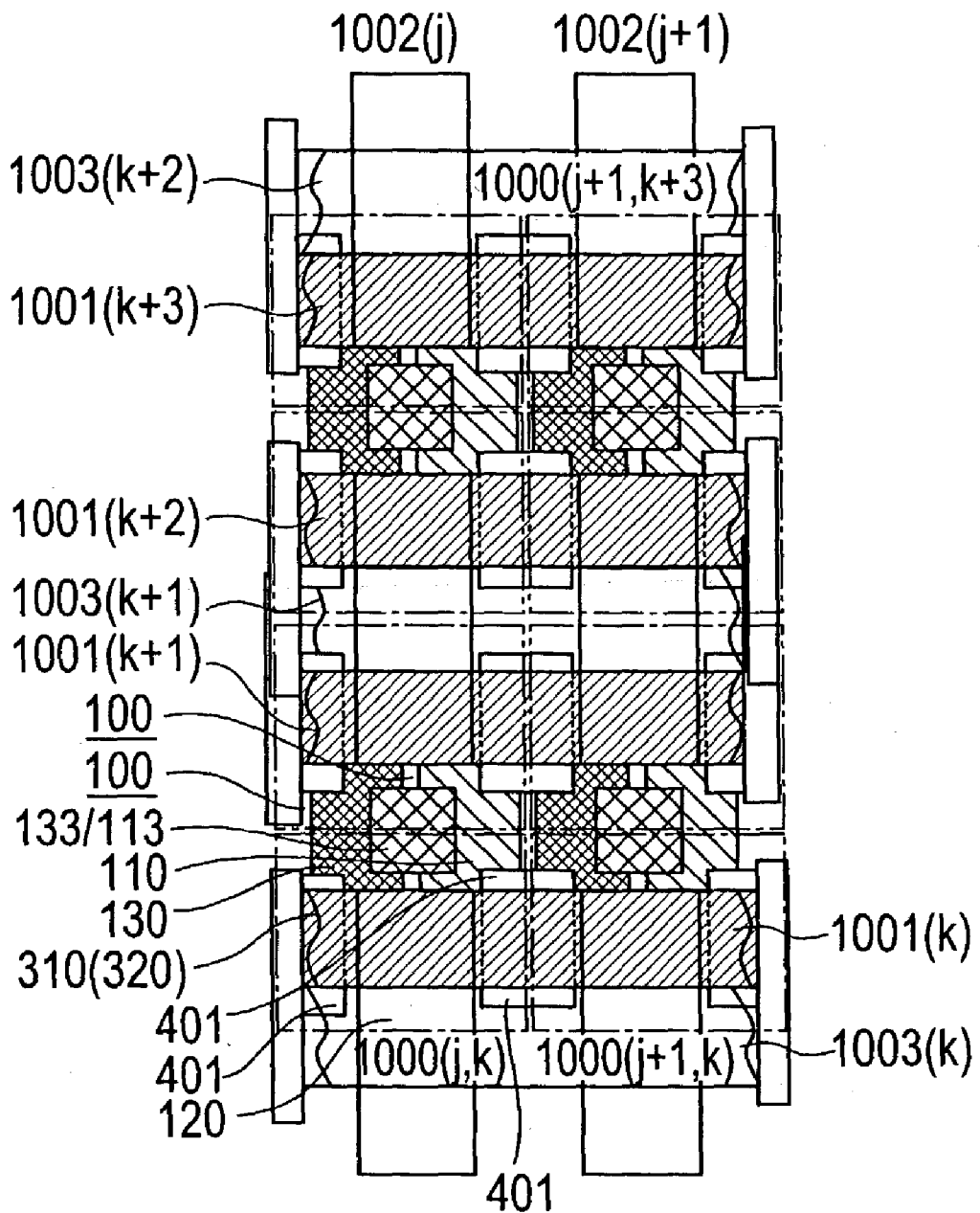
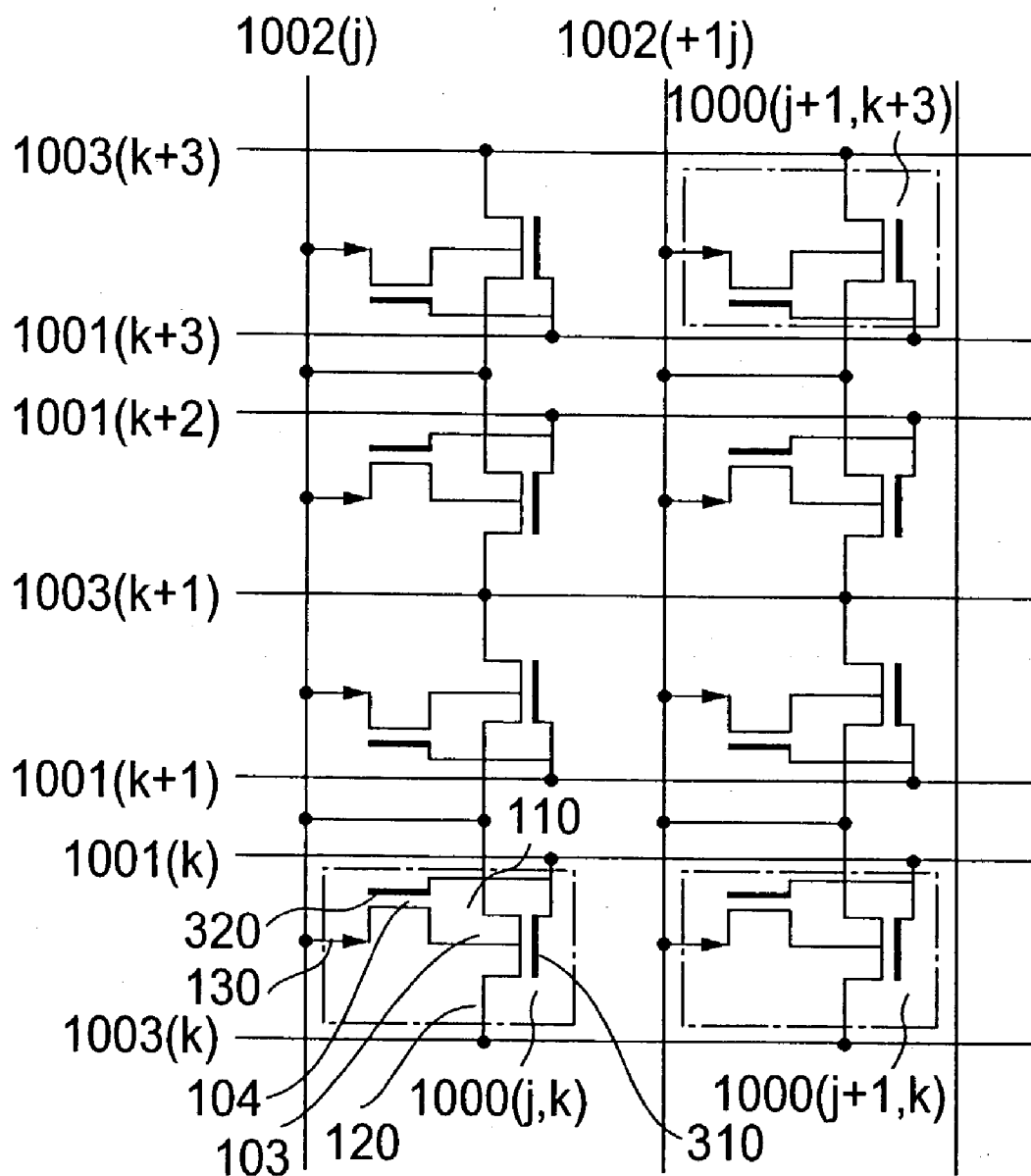


FIG. 9



THIN FILM MEMORY, ARRAY, AND OPERATION METHOD AND MANUFACTURE METHOD THEREFOR

BACKGROUND OF THE INVENTION

[0001] 1. Field of the Invention

[0002] The present invention relates to a semiconductor memory and an integrated circuit built therefrom, and more specifically, to a technique which uses for a channel formation region a semiconductor thin film such as SOI (Semiconductor On Insulator) or SON (Semiconductor On Nothing). The semiconductor thin film is formed on an insulating substrate (SOI) in some cases, is suspended and held at both ends by substrates in a hollow state (SON) in some other cases, and has a projecting portion which is connected at one end to a substrate in still other cases.

[0003] 2. Description of the Related Art

[0004] H. J. Wann et al. have proposed in 1993 to obtain a dynamic memory that does not use a capacitor by incorporating two complementary transistors in a partially depleted SOIMOS transistor structure (See Non-patent Document 1, for example).

[0005] Recently, a memory has been proposed in which carriers are generated utilizing a carrier multiplication phenomenon such as avalanche breakdown in a drain high electric field region of a partially depleted SOIMOS transistor and the obtained carriers are used to charge a neutral body in order to read a change in current flowing between the drain and the source of the transistor (See Non-patent Document 2, for example).

[0006] The term partially depleted SOI, abbreviated as PD SOI, refers to SOI in which a depletion layer spreads only partially in the depth direction of its semiconductor thin film to give it a neutral region. 'Body' is a simplified term for the above semiconductor thin film in which a channel is formed.

[0007] [Non-Patent Document 1]

[0008] H. J. Wann, C. Hu, "A capacitor-less DRAM cell on SOI substrate", 1993, IEDM (International Electron Device Meeting) Technical Digest, pp. 635-638

[0009] [Non-Patent Document 2]

[0010] S. Okhonin et al., "A Capacitor-less IT-DRAM Cell", IEEE Electron Device Letters, Volume 23, Number 2, pp. 85-87, February 2002

[0011] On the other hand, fully depleted (FD) SOI is used for low power consumption uses or for advanced miniaturization of SOIMOS transistor, thereby creating the need for SOI memory cells that can be applied to FDSOI. The term FD (fully depleted) SOI refers to SOI having such thickness and impurity concentration that makes the depletion layer cover the entire depth of the semiconductor thin film.

[0012] The method of utilizing carrier multiplication in a drain high electric field portion also causes carrier multiplication of a small degree in a not-selected cell which is connected to a bit line for driving at high voltage a drain of a cell to which a signal is to be written. This leads to erroneous, albeit mild, writing called write disturb and therefore makes it difficult to assemble a large array in which a large number of cells are connected to each bit line.

SUMMARY OF THE INVENTION

[0013] The present invention has been made in view of the above, and an object of the present invention is therefore to provide a capacitor-less SOI or other semiconductor thin film memory cell and memory cell array which are applicable to FDSOI. Another object of the present invention is to provide an SOI or other semiconductor thin film memory cell and memory cell array in which data is written or erased without using carrier multiplication in a drain high electric field portion, as well as an operation method and manufacture method for the memory cell and array.

[0014] To attain the above objects, the present invention employs a method of supplying carriers from a third semiconductor region, which is not a drain or a source, (1) to a body (2) without using carrier multiplication in a drain high electric field portion.

BRIEF DESCRIPTION OF THE DRAWINGS

[0015] In the accompanying drawings:

[0016] **FIG. 1** is a sectional view showing a principle of the present invention;

[0017] **FIGS. 2A and 2B** are a plan view showing an embodiment of the present invention and a sectional view thereof, respectively;

[0018] **FIG. 3** is a plan view showing another embodiment of the present invention in which a first conductive gate and a second conductive gate are continuous;

[0019] **FIGS. 4A and 4B** are a plan view and a sectional view, respectively, showing another embodiment of the present invention in which a third conductive gate is placed on a second principal surface of a semiconductor thin film;

[0020] **FIGS. 5A and 5B** are a plan view of an embodiment in which memory cells of the present invention are arranged and connected to form an array structure and a sectional view of a cell portion, respectively;

[0021] **FIGS. 6A to 6G** are sectional views showing an example of a process of manufacturing the memory cells and array of the embodiment shown in **FIGS. 5A and 5B**;

[0022] **FIG. 7** is an equivalent circuit diagram of the memory cell array shown in **FIGS. 5A and 5B**;

[0023] **FIG. 8** is a plan view of memory cells and array in which a writing bit line and a reading bit line are shared; and

[0024] **FIG. 9** is an equivalent circuit diagram of the memory cell array of **FIG. 8**.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0025] Embodiment Mode

[0026] A memory cell of the present invention is shown in **FIG. 1** and **FIGS. 2A and 2B**. **FIG. 1** is an example of a sectional view thereof. **FIG. 2A** is an example of a plan view thereof and **FIG. 2B** is a sectional view taken along the line X-X' of **FIG. 2A**. As shown in these drawings, the memory cell includes:

[0027] a semiconductor thin film **100** having a first principal surface **101** and a second principal surface **102** that faces the first principal surface;

[0028] a first gate insulating film **210** formed on the first principal surface of the semiconductor thin film;

[0029] a first conductive gate **310** formed on the first gate insulating film;

[0030] a first semiconductor region **110** and a second semiconductor region **120** which face each other across the first conductive gate, which are insulated from the first conductive gate, which are in contact with the semiconductor thin film **100**, and which have a first conductivity type; and

[0031] a third semiconductor region **130** which has the opposite conductivity type and which is in contact with the semiconductor thin film.

[0032] The semiconductor thin film **100** has such a combination of thickness and impurity concentration relation that the first conductive gate electric potential causes depletion of carriers between the first principal surface **101** and the second principal surface **102** between the first and second semiconductor regions below the first conductive gate.

[0033] In the memory cell provided by the present invention, the semiconductor thin film is extended to the third semiconductor region **130** from a semiconductor thin film portion which is sandwiched between the first semiconductor region **110** and the second semiconductor region **120** and which is denoted by **103**, and on the extended portion of the semiconductor thin film which is denoted by **104**, a second gate insulating film **320** is formed and a second conductive gate is formed on the second gate insulating film **320**.

[0034] In FIGS. 2A and 2B, reference symbol **421** represents an inter-gate insulating film which is provided, if necessary, to insulate the first conductive gate and the second conductive gate. Denoted by **400** is a so-called field insulating film. **413** and **431** represent an insulating film formed on the third semiconductor region and an insulating film on the first conductive gate, respectively. **113**, **123**, **133**, **313**, and **323** are provided, if necessary, to serve as contacts leading to the first, second, and third semiconductor regions and contacts leading to the first and conductive gates. FIG. 1 corresponds to a sectional view taken along the line Y-Y' in FIG. 2A. It is not always necessary for each cell to have the above contacts. In particular, a contact leading to a conductive gate can be shared among a large number of cells since a conductive gate often constitutes a part of a word line.

[0035] A first conductivity type channel is induced in the semiconductor thin film portion **103** that is sandwiched between the first semiconductor region **110** and the second semiconductor region **120** by the electric potential exceeding the gate threshold voltage of the first conductive gate. In the present invention, the semiconductor thin film portion **103** is called a first channel formation semiconductor thin film portion.

[0036] In the semiconductor thin film extended portion **104**, carriers of the opposite conductivity type are induced, or a channel for carriers of the opposite conductivity type is formed by the electric potential relation between the second conductive gate and the third semiconductor region. The extended portion **104** is called in the present invention as a second channel formation semiconductor thin film portion.

A portion **105** which is different in conductivity type or impurity concentration from the extended portion **104** may be formed in the extended portion **104** in order to adjust the gate threshold voltage of the opposite conductivity type carrier channel which is viewed from the second conductive gate. In the present invention, the above expression 'electric potential exceeding the gate threshold voltage' means an electric potential whose absolute value is larger than the gate threshold voltage in the positive direction if the transistor is an n-channel transistor and an electric potential whose absolute value is larger than the gate threshold voltage in the negative direction if the transistor is a p-channel transistor.

[0037] The distance between the first principal surface and the second principal surface is called in the present invention as the thickness of the semiconductor thin film.

[0038] By a first combination of the electric potential relation between the second conductive gate and the third semiconductor region, carriers **2** of the opposite conductivity type are implanted from the third semiconductor region through the second channel formation semiconductor thin film portion into the first channel formation semiconductor thin film portion to change the gate threshold voltage of the first conductive channel in the first channel formation semiconductor thin film portion which is viewed from the first conductive gate into a first value $V_{th1,1}$. This operation is called 'writing' in the present invention.

[0039] According to the first combination of the electric potential relation, a value obtained by subtracting the electric potential of the third semiconductor region from the electric potential of the second conductive gate exceeds a gate threshold voltage $V_{th2,2}$ of the channel that is placed in the second channel formation semiconductor thin film portion to deliver the opposite conductivity type carriers from the third semiconductor region. $V_{th2,2}$ is the gate threshold voltage viewed from the second conductive gate.

[0040] With carriers of the opposite conductivity type implanted to the first channel formation semiconductor thin film portion, a gate voltage necessary for the first conductive gate to induce the first conductivity channel is reduced by a level corresponding to the number of the implanted carriers of the opposite conductivity type or electric charges. This means that the gate threshold voltage has shifted toward the depression side equivalently. If the gate threshold voltage changes in an enhancement type range, it means that the absolute value of the gate threshold voltage is reduced.

[0041] The first electric potential combination allows multilevel setting. For example, on the premise that a value obtained by subtracting the electric potential of the third semiconductor region from the electric potential of the second conductive gate sufficiently exceeds a gate threshold voltage $V_{th2,r}$ of the channel that is placed in the second channel formation semiconductor thin film portion to deliver the opposite conductivity type carriers from the third semiconductor region which is viewed from the second conductive gate, the electric potential of the third semiconductor region with respect to the gate electric potential is set to multilevel. This makes it possible to change the gate threshold voltage of the first conductive channel which is viewed from the first conductive gate into multilevel values $V_{th1,1}$, $V_{th1,2}$, $V_{th1,3}$. . . for writing. In short, this makes it possible to store plural bit information in one cell.

[0042] The opposite conductivity type carriers **2** implanted into the first channel formation semiconductor

thin film portion gradually diminish because of recombination with carriers of the first conductivity type or efflux from the first channel formation semiconductor thin film portion due to self-field. Accordingly, it is necessary to read the amount of opposite conductivity carriers accumulated in the first channel formation semiconductor thin film portion and re-write based on the readout. This is called 'refreshing'.

[0043] By a second combination of the electric potential relation between the second conductive gate and the third semiconductor region, the carriers 2 of the opposite conductivity type are drawn into the third semiconductor region from the first channel formation semiconductor thin film portion to change the gate threshold voltage of the first conductive channel in the first channel formation semiconductor thin film portion which is viewed from the first conductive gate into a second value V_{th10} . This operation is called 'erasing' in the present invention.

[0044] According to the second combination of the electric potential relation, a value obtained by subtracting the electric potential of the opposite conductivity type carriers implanted into the first channel formation semiconductor thin film portion from the electric potential of the second conductive gate exceeds the gate threshold voltage V_{th2r} of the opposite conductivity type channel in the second channel formation semiconductor thin film portion which is viewed from the second conductive gate.

[0045] Alternatively, the erasing operation is achieved by giving an electric potential of a direction that attracts carriers of the opposite conductivity type to the first or second semiconductor region (for instance, 0.6 V or higher in the negative direction for holes). In this case, carriers of the first conductivity type are also supplied to the first channel formation semiconductor thin film portion to accelerate a decrease of carriers of the opposite conductivity type through recombination. In this erasing operation, data is erased from every cell whose second semiconductor region or first semiconductor region is connected to a common line or bit line.

[0046] Information stored in a memory cell of the present invention is judged by whether or not carriers of the opposite conductivity type are accumulated in the first channel formation semiconductor thin film portion of the memory cell or from the accumulation amount. To judge stored information in this way, the voltage of the first conductive gate with respect to the second semiconductor region is set to a prescribed value that exceeds one or both of the first gate threshold voltage and the second gate threshold voltage and whether a current flowing between the first semiconductor region and the second semiconductor region is large or small is detected ('small' including zero). For instance, the voltage of the first conductive gate with respect to the second semiconductor region is set to a level between the first gate threshold voltage and the second gate threshold voltage and whether or not a current flows between the first semiconductor region and the second semiconductor region is detected to judge the stored information.

[0047] In the case where multilevel of first gate threshold voltages are written, the voltage of the first conductive gate is set to a level between any two out of those levels to identify the stored data. Alternatively, the voltage of the first conductive gate with respect to the second semiconductor region is set to a voltage that exceeds both the first gate

threshold voltage and the second gate threshold voltage and the stored information is judged from the amount of current flowing between the first semiconductor region and the second semiconductor region.

[0048] For detection of the current, a known method such as comparative detection using a reference current and a comparative circuit, or detection by time constant of charging or discharging a bit line or other capacitance can be employed. This operation is called 'reading'.

[0049] Through the reading operation, the electric potential of the valence band or conduction band in the energy band of the first channel formation semiconductor thin film portion is moved in a direction that eliminates carriers of the opposite conductivity type. In addition, a large amount of first conductivity type carriers are supplied to first channel formation semiconductor thin film portion to accelerate recombination of opposite conductivity type carriers accumulated in the first channel formation semiconductor thin film portion and to cause information loss in some cases. In this case, the refreshing operation has to be conducted immediately after reading.

[0050] The semiconductor thin film 100 in FIG. 1 is supported by a substrate 10 having an insulating layer 20 formed on its surface. In most cases, the substrate 10 is formed of silicon and the insulating layer 20 is a silicon oxide film. The supporting substrate that has an insulating layer on its surface is called an insulating substrate. An insulating substrate that is entirely formed of an insulating material, such as a quartz substrate, can also serve as the supporting substrate. An alternative structure is that at least one end of the semiconductor thin film, or an end of the first semiconductor region, the second semiconductor region, or the third semiconductor region, is supported by a substrate.

[0051] In the present invention, if voltages of the first conductive gate and the second conductive gate during the writing, erasing, and reading operations are chosen carefully, the same voltage can be used for each operation mode. Then the first and second conductive gates can be made continuous or shared as FIG. 3 shows its example. Furthermore, the same material and thickness can be employed for the gate insulating films. As a result, the number of manufacture steps and the area the cell occupies are reduced. In this case, by replacing the 'second conductive gate' in the description on the writing and erasing operations of the present invention with the 'first conductive gate', it becomes possible to realize the writing and erasing operations.

[0052] It is also possible in the present invention to write the first gate threshold voltage value under a certain condition and the second gate threshold voltage value under another condition. For example, the first gate threshold voltage is written when a value obtained by subtracting the electric potential of the third semiconductor region from the electric potential of the second conductive gate sufficiently exceeds a gate threshold voltage V_{th2r} of the channel that is placed in the second channel formation semiconductor thin film portion to deliver the opposite conductivity type carriers from the third semiconductor region which is viewed from the second conductive gate while the electric potential of the third semiconductor region is biased forward with respect to the electric potential of the second semiconductor region. On the other hand, the second gate threshold voltage is written (equals to erasing) when the electric potential of the

third semiconductor region is zero-biased or biased backward with respect to the second gate voltage.

[0053] Another mode of a preferred memory cell for effectively carrying out the present invention is a memory cell shown in FIGS. 4A and 4B. The memory cell is characterized by including at least:

[0054] a semiconductor thin film (broken into portions 103 and 104) having a first principal surface 101 and a second principal surface 102 that faces the first principal surface;

[0055] a first gate insulating film 210 formed on the first principal surface of the semiconductor thin film;

[0056] a first conductive gate 310 formed on the first gate insulating film;

[0057] a first semiconductor region 110 and a second semiconductor region 120 which face each other across the first conductive gate, which are insulated from the first conductive gate, which are in contact with the semiconductor thin film, and which have a first conductivity type;

[0058] a third semiconductor region 130 which has the opposite conductivity type and which is in contact with the semiconductor thin film;

[0059] a third gate insulating film 230 formed on the second principal surface of the semiconductor thin film portion (first channel formation semiconductor thin film portion) 103 that is sandwiched between the first semiconductor region and the second semiconductor region; and

[0060] a third conductive gate 330 which is in contact with the third gate insulating film 230. The semiconductor thin film portion 104 is also called as a second channel formation semiconductor thin film portion in the present invention.

[0061] Carriers of the opposite conductivity type are stably accumulated in the first channel formation semiconductor thin film portion if the third conductive gate is given an electric potential exceeding a gate threshold voltage V_{th3} , which is the gate threshold voltage viewed from the third conductive gate with respect to opposite conductivity type carriers induced in the first channel formation semiconductor thin film portion. However, the refreshing operation is necessary in this case too, for carriers of the opposite conductivity type are gradually generated and accumulated in the first channel formation semiconductor thin film portion by thermal excitation, slight carrier multiplication in normal electric field, and the like after the erasing operation.

[0062] FIG. 4A is a plan view of the thin film memory cell of the above embodiment and FIG. 4B is a sectional view taken along the dot-dash line X-X' of the plan view of FIG. 4B. In FIGS. 4A and 4B, reference symbol 10 denotes a supporting substrate and 20, an insulating film on a surface of the supporting substrate 10. Denoted by 103 and 104 are the first and second channel formation semiconductor thin film portions, respectively, which are a part of the semiconductor thin film 100. 210 and 220 represent gate insulating films formed on the semiconductor thin film portions 103 and 104. The gate insulating films 210 and 220 in the drawing are continuous. Denoted by 310 is the first conduc-

tive gate, which is also continuous from the second conductive gate. 110 and 120 are the first and second semiconductor regions, respectively. 130 denotes the third semiconductor region.

[0063] 113 and 123 represent wiring contacts leading to the first and second semiconductor regions, respectively. 133 represents a wiring contact leading to the third semiconductor region. Denoted by 400 is a so-called field insulating film which is placed under a wire or the like. 431 denotes an insulating film placed on the first conductive gate, and 410, an insulating film placed between the semiconductor thin film 100 and the insulating film 20. 313 denotes a wiring contact leading to the first conductive gate. 333 denotes a wiring contact provided, if necessary, to lead to the third conductive gate.

[0064] It is not always necessary for each cell to have the above contacts. In particular, a contact leading to a conductive gate can be shared among a large number of cells since a conductive gate often constitutes a part of a word line. An impurity region 105 is not always necessary if the electric field of the third conductive gate influences the portion 104 less than the portion 103 (in other words, if the third conductive gate does not overlap the portion 104 as shown in FIG. 4B or if the third conductive film overlaps the portion 104 while an insulating film thicker than the film 230 is sandwiched between the two).

[0065] In the embodiments described above, the first and second conductive gates can have different gate threshold voltages if the conductivity type of an impurity or impurity concentration of the second channel formation semiconductor thin film portion, or the second conductive gate material is different from the conductivity type of an impurity or impurity concentration of the first channel formation semiconductor thin film portion, or the first conductive gate material. Opposite conductivity type carriers implanted to the second channel formation semiconductor thin film portion is prevented from flowing back to the third semiconductor region if the gate threshold voltage of the second conductive gate with respect to the channel for opposite conductivity type carriers from the third semiconductor region is set to a level further in the enhancement type direction than the gate threshold voltage of the first conductive gate.

[0066] Embodiments

[0067] Described below is the memory cell operation of when the first conductivity type is the n type and the opposite conductivity type is the p type. The principles and effects given in the following description also apply to the case where the first conductivity type is the p type, although the direction of symbol changes is reversed. FIG. 5A is a plan view of an embodiment of memory cells of the present invention and an array of the memory cells. FIG. 5B is a sectional view taken along the dot-dash line X-X' of the plan view of FIG. 5A.

[0068] Reference symbol 10 denotes a supporting substrate, which, in this example, is an n type silicon <100> plane wafer of high resistance. Denoted by 20 is a silicon oxide film with a thickness of about 100 nm. 103 represents a semiconductor thin film about 30 nm in thickness which serves as a first channel formation semiconductor thin film portion of a thin film memory cell 1000 of this embodiment.

104 represents a second channel formation semiconductor thin film portion. **105** represents a high impurity concentration portion in the second channel formation semiconductor thin film portion. **110** represents a drain (first semiconductor region). **114** is a drain extension. **120** is a source (second semiconductor region). **124** represents a source extension. **130** is a third semiconductor region of the opposite conductivity type. **210** is a first gate oxynitride film with a thickness of 2.7 nm. **220** is a second gate oxynitride film. **310** and **320** are a first conductive gate and a second conductive gate that is continuous from the first conductive gate. **300** is a symbol as a conductive gate thin film. **1001** is a functional symbol as a local (partial) word line.)

[0069] **210** and **220** are continuous gates. The first conductive gate is about 100 nm in length and, in this embodiment, is formed from a silicon thin film doped with boron. The first, second, and third semiconductor regions include a semiconductor film that is formed on the semiconductor thin film through epitaxial growth. The first and second channel formation semiconductor thin film portions **103** and **104** in one cell are separated from the first and second channel formation semiconductor thin film portions **103** and **104** in an adjacent cell by a separation insulating film **401**.

[0070] Denoted by **113** is a contact leading to the first semiconductor region, and the contact is connected to a reading bit line **1005**. **113** represents a contact leading to the third semiconductor region and the contact is connected to a writing bit line **1004**. The continuous first and second conductive electrodes **310** (**320**) are continuously extended between cells in the word direction, thereby forming a partial common line **1001**. The second semiconductor region is extended between cells in the word direction, thereby forming a partial common line **1003**. The partial word line and the partial common line are extended as long as the direct resistance does not affect the array operation, and are respectively connected to a global word line and a global common line through a selection transistor or directly. In a large capacitance array, the above two types of bit lines are also connected to their respective global bit lines through a selection transistor.

[0071] In the array arrangement of FIG. 5A, cells **1000** are repeatedly arranged in the bit direction to form a mirror image relation. As a result, the contacts **113** and **133** are shared between cells adjacent to each other in the bit direction. The first and third semiconductor regions are continued from a cell to its adjacent cell in one way of the bit direction whereas the second semiconductor region is continued from a cell to its adjacent cell in the other way in the bit direction. The array area is thus reduced. FIG. 5A shows two cells in the word direction and four cells in the bit direction, eight cells in total (a cell **1000** (j, k), . . . , a cell **1000** (j+1, k+3)). The mirror image arrangement of cells is also employed in an embodiment of FIG. 8 which will be described later.

[0072] A manufacture process of this embodiment is described below with reference to sectional views of FIGS. 6A to 6G and FIG. 5B.

[0073] (a) A highly resistive silicon wafer is used as a supporting substrate **10** and a silicon oxide film **20** with a thickness of about 100 nm and a silicon thin film **100** which has an n type impurity concentration of about 2×10^{17} atoms/cc and which has a thickness of about 35 nm are layered on the substrate to prepare an SOI substrate.

[0074] (b) On the thus obtained SOI, an oxide film **41** is let grow until it reaches a thickness of about 7 nm by thermal oxidation and a silicon nitride film **42** with a thickness of about 50 nm is formed thereon by CVD. Thereafter, a photoresist pattern **51** is formed by known photolithography to leave necessary portions of the silicon thin film such as regions where memory cells are connected in the word direction and the bit direction, selection transistor regions, and peripheral circuit regions.

[0075] (c) Using the photoresist pattern **51** as a mask, the silicon nitride film is etched under etching conditions that provide a selective ratio with respect to the silicon oxide film. The photoresist pattern is then removed and the substrate surface is cleaned. The exposed surface of the silicon oxide film which is exposed by the removal of the silicon nitride film is oxidized by pyrogenic oxidation until a silicon oxide film **401** grows to a thickness of about 60 nm. Through this step, the silicon thin film **100** is divided into pieces leaving the necessary portions given in the above.

[0076] Alternatively, a known STI (shallow trench isolation) technique may be used to divide the silicon thin film. An insulating film for dividing the silicon thin film in the planar direction is called an insulating separation film **401**.

[0077] The silicon nitride film **42** is removed by a hot phosphoric acid-based etchant and the silicon oxide film **41** is removed by a buffer hydrofluoric acid-based etchant to expose the surface of the silicon thin film **100**.

[0078] A silicon oxide film **200** is formed on the surface of the silicon thin film **100** by thermal oxidation to a thickness of 2.7 nm. Thereafter, ECR (Electron Cyclotron Resonance), ICP (Inductively Coupled Plasma), or like other high density plasma apparatus is used for surface nitrogenization at a nitrogenization ratio of 5 to 7% by introducing nitrogen radical from plasma of nitrogen gas, hydrogen gas, or xenon gas to the substrate surface and setting the substrate temperature to 400° C. Then the substrate is transferred in a highly pure nitrogen gas atmosphere and subjected to heat treatment at 800° C. in nitrogen to anneal surface defects. The silicon oxide film thus nitrogenized is used as the first and second gate oxide films.

[0079] (d) Next, a conductive gate thin film **300** is formed by deposition. For the first 10 nm or so, pure silicon is deposited to form a pure silicon thin film **301**. Then a boron-doped silicon thin film **302** is formed by deposition to a thickness of 200 nm. The material gas used are monosilane (SiH_4) and di-borane (B_2H_6). A silicon nitride film **43** is formed thereon by deposition to a thickness of about 100 nm. Ion implantation may be employed for the above boron doping.

[0080] Using a known technique such as ArF lithography or electron beam lithography, a gate-shaped photoresist pattern for a conductive gate/local word line having a gate length of about 100 nm is formed on the above silicon nitride film/conductive gate thin film. The photoresist pattern is used as a mask to etch the silicon nitride film and the conductive gate thin film in order by the RIE technique.

[0081] A photoresist film shaped by photolithography and the silicon nitride film/conductive gate thin film are used as selection masks to selectively form, by ion implantation at low acceleration voltage (about 15 KeV for arsenic), an extension region (**114**) of the n type drain (the first semi-

conductor region) and an extension region (124) of the source (the second semiconductor region). In the implantation, the dose is set so as to obtain an impurity concentration of about 1×10^{19} atoms/cc (which is about 3×10^{13} atoms/cm²).

[0082] Similarly, a photoresist film shaped by photolithography and the silicon nitride film/conductive gate thin film are used as selection masks to selectively implant arsenic in the portion that forms the third semiconductor region at a dose of about 8.5×10^{12} atoms/cc. A high impurity concentration region 105 is thus formed in the second channel formation semiconductor thin film portion so that it is in contact with the third semiconductor region formed in the subsequent step. This shifts the gate threshold voltage V_{th2r} of the channel for holes from the third semiconductor region which is viewed from the second conductive gate to the enhancement side.

[0083] (e) Using a known gate side wall insulating film process, insulating film side walls 403 each having a thickness of about 30 nm are formed on the side faces of the first and second conductive gates. The side walls are a two-layer laminate consisting of a silicon nitride film 404 with a thickness of about 7 nm and a silicon oxide film 405 with a thickness of about 23 nm. At this stage, the silicon nitride film 404 is left on the semiconductor thin film.

[0084] Lithography is used to form a photoresist pattern having an opening in the portion where the third semiconductor region is to be formed. A portion of the silicon nitride film 404 under the opening is etched by RIE. Then the photoresist is removed and the silicon oxide film remaining in the opening is subjected to wet etching, followed by hydrogen termination.

[0085] A boron-doped silicon crystal film 135 is selectively grown in the opening until it reaches a thickness of about 100 nm. The boron concentration is about 4×10^{19} atoms/cc. Through thermal oxidation at 850° C., an oxide film 406 with a thickness of about 30 nm is let grow on the top and side faces of the p type silicon crystal film. In actuality, boron is diffused at this point from the silicon crystal film 135 into the semiconductor thin film 100 to give a portion of the semiconductor thin film that is under 135 the p type conductivity. In FIG. 6E, the portion is distinguished from the silicon crystal film selectively grown.

[0086] (f) The silicon nitride film 401 left on the memory cell portions of the semiconductor thin film 100 is etched by RIE. The silicon oxide film remaining on the etching surface is subjected to wet etching and then hydrogen termination is conducted. In etching the silicon nitride film, a portion of the silicon nitride film is excluded which is under the oxide film 406 on the side face of the crystal thin film that has been selectively grown to form the semiconductor region 130.

[0087] Arsenic-doped silicon crystal films 115 and 125 are selectively grown in the opening to a thickness of about 100 nm each. The arsenic concentration is about 5×10^{20} atoms/cc. The oxide film 406 on the side face separates the p type high impurity concentration silicon crystal film 135 from the n type high impurity concentration silicon crystal films 115 and 125.

[0088] Instead of the above selective crystal growth, selective ion implantation using as masks a photoresist pattern

and the conductive gate thin film and the silicon nitride film thereon may be employed to form the first, second, and third semiconductor regions.

[0089] During crystal growth and subsequent heating step, impurities of these silicon crystal films obtained through selective crystal growth are diffused into the semiconductor thin film 100 starting from points where the crystal films and the semiconductor thin film meet. As a result, the third semiconductor region 130, the first semiconductor region 110, and the second semiconductor region 120 are formed at the same time the silicon crystal thin films are formed by selective crystal growth.

[0090] (h) The silicon nitride film 43 on the conductive gate thin film (300) is subjected to wet etching by hot phosphoric acid or the like. The surface is then washed, nickel is deposited by evaporation to a thickness of about 20 nm, and next follows sintering. The nickel on the insulating film that has not reacted is etched by an acid to leave a nickel silicide layer. Through high temperature sintering, a silicide layer 110s is formed on the first semiconductor region (drain), a silicide layer 120s is formed on the second semiconductor region (source), and a silicide layer 300s is formed on the gate thin film.

[0091] A silicon oxide film is formed as a wiring interlayer insulating film 440 by CVD on the surface. Contact holes are opened in the film as needed and contact plugs 133 and 113 are formed from titanium nitride, tungsten, or the like. Then a TiN thin film and a tungsten thin film are formed by evaporation. A wiring pattern is formed by photolithography and RIE (reactive ion etching) to obtain a local writing bit line 1004 and a local reading bit line 1005 (at this point, the state of FIG. 5B is reached) Thereafter, an interlayer insulating film and a multi-layer wire composed of an Al wire, a copper wire or the like are formed as needed and, lastly, a passivation film is formed.

[0092] The features of this embodiment are (1) that the third semiconductor region and the first semiconductor region are insulated by the insulating film 406 formed on the side face of the crystal thin film that is obtained by selective epitaxial growth and (2) that the gate threshold voltage for inducing carriers of the opposite type differs from the first channel formation semiconductor thin film portion to the opposite conductivity type carrier channel which leads to the first channel formation semiconductor thin film portion from the third semiconductor region.

[0093] Since the opposite conductivity type carrier channel which leads to the first channel formation semiconductor thin film portion from the third semiconductor region crosses the high impurity concentration region 105 in contact with the first channel formation thin film portion, the impurity concentration of the second channel formation thin film portion differs from that of the first channel formation thin film portion. Thus, the gate threshold voltage which induces the carriers of the opposite conductivity type differs between the first channel formation thin film portion and the opposite conductivity type carrier channel which leads to the first channel formation semiconductor thin film portion from the third semiconductor region.

[0094] If a barrier against carriers of the opposite conductivity type is formed between the first channel formation semiconductor thin film portion and the third semiconductor

region as described above, it reduces the amount of opposite conductivity type carriers pushed back to the third semiconductor region upon reading where a voltage in the direction that induces carriers of the first conductivity type is applied to the first conductive gate. Therefore reading can be carried out without fear of erasing the accumulated information.

[0095] In the embodiment illustrated in **FIGS. 5A and 5B**, the first semiconductor regions of cells arranged in the longitudinal direction are connected to the reading bit line **1005** and the third semiconductor regions of these cells are connected to the writing bit line **1004**. The first and second common conductive gates of cells arranged in the lateral direction are connected to the word line **1001**. The second semiconductor regions of the cells arranged in the lateral direction are connected to the common line **1003**. The reading bit line and the writing bit line extend in the longitudinal direction whereas the word line and the common line stretch in the lateral direction. Alignment of cells and the vertical and horizontal relation of the bit line and the word line can be reversed without causing any problem.

[0096] A description is given below on the operation of a single cell that is manufactured in accordance with the above embodiment. Data is written in this cell by setting the electric potential of the second conductive gate with respect to the electric potential of the third semiconductor region to a level that exceeds the threshold voltage V_{th2} of the opposite conductivity type carrier channel below the second conductive gate.

[0097] In the cell manufactured by the above manufacture process, V_{th2} is about -0.5 V when the electric potential of the second semiconductor region is 0 V and therefore it is desirable to set the electric potential of the third semiconductor region to 0.2 to 0.3 V while setting the second conductive gate to -0.3 to -0.4 V. To keep data, setting the first conductive gate to 0 to 0.2 V and giving the first semiconductor region the same electric potential as the second semiconductor region are desirable.

[0098] To erase data, the second semiconductor region is set to -0.6 V or lower (when the electric potential of the first semiconductor region is 0 V and the first conductive gate is 0 V), or the electric potential of the third semiconductor region is set to 0 to -0.4 V and the electric potential of the second conductive gate is set to -0.55 V or lower. In this

way, opposite conductivity type carriers (holes) accumulated in the first channel formation semiconductor thin film portion are drawn into the second semiconductor region or into the third semiconductor region.

[0099] To read data, whether the current flowing between the first and second semiconductor regions is large or small is detected by applying, to the first conductive gate, a voltage about the first conductivity type carrier gate threshold voltage V_{th10} (0.2 V larger at most) of the first conductive gate in the cell whose data has been erased. In the case of multi-valued storing, a voltage between V_{th10} and V_{th11} , a voltage between V_{th11} and V_{th12} , a voltage between V_{th12} and V_{th13} . . . are applied to the first conductive gate to detect stored information. A voltage applied between the first and second semiconductor regions is from 0.2 V to 0.9 V. The intermediate current value between the current of a cell to which data is written and the current of a cell from which data is erased is taken to serve as the criterion. In the case where a voltage between one stored threshold voltage and another stored threshold voltage is applied to the first conductive gate, information is judged from the presence or absence of the cell current.

[0100] In order to prevent writing error caused by opposite polarity carriers generated in the high electric field region of the first channel formation semiconductor thin film portion, it is safer to avoid applying a voltage equal to or larger than the energy gap value of the semiconductor thin film which is converted into voltage (1.1 V if the film is silicon) between the first and second semiconductor regions.

[0101] In Embodiment 1, cells of the present invention in **FIGS. 5A and 5B** are connected as shown in an equivalent circuit diagram of **FIG. 7** to obtain a memory array. The memory array is operated by combination of voltages shown in Table 1 below. This array is suitable as a memory for a specific use because data can be written in cells of a word while data is read from cells of another word. The array is also suited for high speed refreshing operation. Table 1 shows the voltage relation among the word line, the writing bit line, the reading bit line, and the common line when the array is operated by a unipolar power supply of 1.2 V. Operation on a unipolar power supply is made possible by biasing the common line at a positive electric potential, usually, 0.5 V.

TABLE 1

Operation Voltage Example of a Memory Array according to Embodiment 1 of the Present Invention												
	Selected cell voltage (V)				Non-selected cell voltage (V)							
					Writing		Erasing		Reading			
	Writing	Erasing	Reading	Keeping	CW	CB	CW	CB	CW	CB	Keeping	
Wordline	0.1	0	1.2	0.5	0.1	0.5	0	0.5	1.2	0.5	0.5	
Writing bit line	0.7	0	0.5	0.5	0.5	0.7	0	0	0.5	0.5	0.5	
Reading bit line	0.5	0.5	0.8	0.5	0.5	0.5	0.5	0.5	0.5	0.8	0.5	
Common line	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	

CW (common word): cells sharing a word line
CB (common bit): cells sharing a bit line

[0102] In the operation shown in Table 1, data is erased from all cells that are connected to the same word line upon erasing. An acceptable change in voltage of one line is within ± 0.1 V when the voltage of another line has the standard value. If the voltage of every line is changed in the same direction, the acceptable electric potential change is larger.

[0103] It is sufficient if the difference between the electric potential of each line and the electric potential of the common line satisfies the relation shown in Table 1. Accordingly, it may also be expressed as Table 2.

[0107] The semiconductor thin film 100 extending in the word direction which includes the first semiconductor region and the third semiconductor region is physically continuous. On the other hand, in the example shown in FIGS. 5A and 5B, the first semiconductor regions in adjacent cells in the word direction are separated by an insulating film. However, if the distance between the writing bit line and the reading bit line is narrowed by, for example, forming the two bit lines from different wiring layers, FIGS. 5A and 5B can also take a structure in which the semiconductor thin film is continuous on the first semiconductor region side too and the

TABLE 2

Relative Expression of Operation Voltage Example of a Memory Array according to Embodiment 1 of the Present Invention				
Selected cell voltage (V)				
	Writing	Erasing	Reading	Keeping
Word line	Common line electric potential −0.4	Common line electric potential 0.5	Common line electric potential +0.7	Common line electric potential
Writing bit line	Common line electric potential +0.2	Common line electric potential	Common line electric potential	Common line electric potential
Reading bit line	Common line electric potential	Common line electric potential	Common line electric potential +0.3	Common line electric potential

[0104] According to the array structure for memory cells of the present invention, the third semiconductor region and the first semiconductor region are connected to the same bit line (one bit line doubles as a writing bit line and a reading bit line in the memory array of FIGS. 5A and 5B).

[0105] This array structure makes it possible to reduce the array area. FIG. 8 is a plan view of memory cells used in this array connection and the cell area thereof is $6F^2$ to $4F^2$. To achieve a cell area of $4F^2$, a self-alignment contact technique is needed.

[0106] The cell arrangement in the array of FIG. 8 is similar to the one in FIGS. 5A and 5B; the conductive gates in one cell are above the first, second, and third semiconductor regions and this positional relation is reversed in every other cell in the longitudinal direction while the first, second, and third semiconductor regions in one cell are continuous with those in its adjacent cells in the vertical direction. For instance, the first and third semiconductor regions of the k-th cell in the longitudinal direction are continuous with those in the (k+1)-th cell. The second semiconductor region of the j-th cell is continuous with that of the (j+1)-th cell. The first semiconductor region in one cell and the first semiconductor region in a cell adjacent to the one cell in the word direction are electrically insulated from each other by the third semiconductor region of their adjacent cell with respect to backward bias and a slight forward voltage.

first semiconductor region is electrically insulated by the third semiconductor region.

[0108] In any case, the first channel formation semiconductor thin film portion or the second channel formation semiconductor thin film portion of one cell is separated from that of a cell adjacent to the one cell in the word direction.

[0109] In the plan view of FIG. 8 also, the first conductive gate and the second conductive gate are continuous and are further continued to the first or second conductive gate of a cell adjacent in the lateral direction. The gate has a series resistance component and therefore limits the operation speed. To improve this, a metal wire is used as a main word line and is connected to the conductive gates of a group of cells (for example, 32 to 512 cells form one group) before the series resistance reaches the limit value.

[0110] In Embodiment 2, cells of the present invention in FIG. 8 are connected as shown in an equivalent circuit diagram of FIG. 9 to obtain a memory array. The memory array of Embodiment 2 is operated by combination of voltages shown in Table 3 below.

[0111] Table 3 shows an example of the voltage relation among the word line, the bit line, and the common line when the array is operated by a unipolar power supply of 1 V. Operation on a unipolar power supply is made possible by biasing the common line at a positive electric potential, usually, 0.5 V.

TABLE 3

Operation Voltage Example of a Memory Array according to Embodiment 2 of the Present Invention											
Selected cell voltage (V)				Non-selected cell voltage (V)							
Writing				Writing (CW)		Writing (CB)		Reading			
"1"	"0"	Reading	Keeping	"1"	"0"	"1"	"0"	CW	CB	Keeping	
Word line	0	0	1.0 (first)	0.3	0	0	0.3	0.3	1.0	0.3	0.3
Bit line	0.6	0	0.5	0.3	0.3	0.3	0.6	0	0.3	0.5	0.3
Common line	0.3	0.3	0.3	0.3	0.3	0.3	0.3	0.3	0.3	0.3	0.3

CW (common word): cells sharing a word line
CB (common bit): cells sharing a bit line

[0112] The word line voltage upon reading is supplied before the bit line voltage.

[0113] An acceptable change in voltage of one line is within ± 0.1 V when the voltage of another line has the standard value. If the voltage of every line is changed in the same direction, the acceptable electric potential change is larger.

[0114] It is sufficient if the difference between the electric potential of each line and the electric potential of the common line satisfies the relation shown in Table 3. Accordingly, it may also be expressed as Table 4.

[0116] The first, second, and third semiconductor regions are described in this specification as "being in contact with" the semiconductor thin film. This contact state is obtained either by introducing impurity atoms into the semiconductor thin film and forming the first, second, and third semiconductor regions in the film or by forming the first, second, and third semiconductor regions on the semiconductor thin film by deposition.

[0117] The present invention may employ a structure for capacitance coupling of the second principal surface or the side face to the first channel formation semiconductor thin

TABLE 4

Relative Expression of Operation Voltage Example of a Memory Array according to Embodiment 2 of the Present Invention				
Selected cell voltage (V)				
Writing				
	"1"	"0"	Reading	Keeping
Word line	Common line electric potential 0.3	Common line electric potential 0.3	Common line electric potential +0.7 (first)	Common line electric potential
Bit line	Common line electric potential +0.3	Common line electric potential 0.3	Common line electric potential +0.2	Common line electric potential

[0115] In the present invention, the semiconductor thin film may be a silicon germanium single crystal thin film or a strained silicon/silicon germanium laminate other than a silicon single crystal thin film. The gate insulating film may be a silicon oxynitride film, a silicon nitride film, an alumina film, a hafnium oxide film, a film of a silicon-hafnium oxide mixture, a zirconium oxide film, or a film of a silicon-zirconium oxide mixture other than a silicon oxide film. The conductive gates may be a tungsten film, a titanium nitride film, or a titanium/titanium nitride laminate other than a polysilicon film or a silicon germanium film. The first, second, and third semiconductor regions may be formed not only in the semiconductor thin film but also on top of the semiconductor thin film, and a metal silicide film or a metal thin film may be added thereon to form a laminate. Thus the present invention can be carried out within a modification range which comes easy to the skilled in the art.

film portion, so that data stored is kept longer and the amount of opposite conductivity type carriers accumulated is increased.

[0118] The present invention is applicable to both PDSOI and FDSOI and, when applied to FDSOI, the present invention can provide effects that have been difficult to attain in prior art.

[0119] The present invention can provide a memory cell having the FDSOIMOS structure and the FDSOIMIS structure as well as the PDSOIMIS structure, and a memory array using the memory cell. The memory cell does not need a large capacitor.

[0120] The memory can be mounted together with FDSOI logic that is capable of low power operation, and the operation voltage of the memory is in a range that matches the range of the low power logic.

[0121] If the cell takes a so-called double gate MIS structure, carriers of the opposite conductivity type are securely accumulated in the memory cell by the electric potential given to the third conductive gate of the cell.

What is claimed is:

1. A thin film memory cell comprising:

- a semiconductor thin film having a first principal surface and a second principal surface that faces the first principal surface;
- a first gate insulating film formed on the first principal surface of the semiconductor thin film;
- a first conductive gate formed on the first gate insulating film;
- a first semiconductor region and a second semiconductor region which face each other across the first conductive gate, which are insulated from the first conductive gate, which are in contact with the semiconductor thin film, and which have a first conductivity type; and
- a third semiconductor region which has the opposite conductivity type and which is in contact with the semiconductor thin film,

wherein a portion of the semiconductor thin film that is sandwiched between the first semiconductor region and the second semiconductor region forms a first channel formation semiconductor thin film portion,

wherein the semiconductor thin film is extended between the first channel formation semiconductor thin film portion and the third semiconductor region of the opposite conductivity type to form a second channel formation semiconductor thin film portion, and

wherein a second gate insulating film is formed on the extended portion of the semiconductor thin film and a second conductive gate is formed on the second gate insulating film.

2. A thin film memory cell according to claim 1, wherein the first conductive gate and the second conductive gate are continuous.

3. A thin film memory cell according to claim 1, wherein the second gate insulating film and the second conductive gate are continuous with the first gate insulating film and the first conductive gate.

4. A thin film memory cell according to claim 1, wherein the extended portion of the semiconductor thin film has a portion whose impurity concentration is different from the impurity concentration of the semiconductor thin film portion that is sandwiched between the first and second semiconductor regions.

5. A thin film memory cell according to claim 1, wherein the extended portion of the semiconductor thin film has an impurity portion whose conductivity type is different from the conductivity type of the semiconductor thin film portion that is sandwiched between the first and second semiconductor regions.

6. A thin film memory cell comprising:

- a semiconductor thin film having a first principal surface and a second principal surface that faces the first principal surface;
- a first gate insulating film formed on the first principal surface of the semiconductor thin film;

a first conductive gate formed on the first gate insulating film;

a first semiconductor region and a second semiconductor region which face each other across the first conductive gate, which are insulated from the first conductive gate, which are in contact with the semiconductor thin film, and which have a first conductivity type; and

a third semiconductor region which has the opposite conductivity type and which is in contact with the semiconductor thin film in a part of area below the first conductive gate in the direction that crosses substantially at right angles with the direction in which the first semiconductor region and the second semiconductor region face each other,

wherein a portion of the semiconductor thin film that is sandwiched between the first semiconductor region and the second semiconductor region forms a first channel formation semiconductor thin film portion, and

wherein the semiconductor thin film is extended between the first channel formation semiconductor thin film portion and the third semiconductor region of the opposite conductivity type to form a second channel formation semiconductor thin film portion.

7. A thin film memory cell according to claim 6, wherein the second channel formation semiconductor thin film portion has a portion whose impurity concentration is different from the impurity concentration of the first channel formation semiconductor thin film portion.

8. A thin film memory cell according to claim 6, wherein the second channel formation semiconductor thin film portion has an impurity portion whose conductivity type is different from the conductivity type of the first channel formation semiconductor thin film portion.

9. A thin film memory cell according to claim 1, wherein the semiconductor thin film is formed on an insulating substrate.

10. A thin film memory cell according to claim 1, wherein at least the one end of the semiconductor thin film is supported by substrate.

11. A thin film memory cell according to claim 1, further comprising:

a third gate insulating film formed on the second principal surface in the portion where the semiconductor thin film is sandwiched between the first semiconductor region and the second semiconductor region; and

a third conductive gate that is in contact with the third gate insulating film.

12. A thin film memory cell according to claim 11, wherein a surface portion of a substrate supporting the semiconductor thin film serves as the third conductive gate.

13. A thin film memory array comprising:

a plurality of word lines;

a plurality of writing bit lines that are insulated from and intersect the word lines;

a plurality of reading bit lines running by the side of the writing bit lines;

a plurality of common lines; and

a plurality of memory cells according to claim 12,

wherein, in a portion where one of the plural word lines, one of the plural writing bit lines, and a reading bit line that runs along the one writing bit line intersect one another, the first and second conductive gates of one of the plural memory cells are connected to the one word line out of the plural word lines,

wherein the first semiconductor region of the one memory cell is connected to the one reading bit line out of the plural reading bit lines,

wherein the second semiconductor region of the one memory cell is connected to one of the plural common lines, and

wherein the third semiconductor region of the one memory cell is connected to the one writing bit line out of the plural writing bit lines.

14. A thin film memory array comprising:

a plurality of word lines;

a plurality of writing bit lines that are insulated from and intersect the word lines;

a plurality of reading bit lines running by the side of the writing bit lines;

a plurality of common lines; and

a plurality of memory cells according to claim 12,

wherein, in a portion where one of the plural word lines, one of the plural writing bit lines, and a reading bit line that runs along the one writing bit line intersect one another, the first conductive gate of one of the plural memory cells is connected to the one word line out of the plural word lines,

wherein the first semiconductor region of the one memory cell is connected to the one reading bit line out of the plural reading bit lines,

wherein the second semiconductor region of the one memory cell is connected to one of the plural common lines, and

wherein the third semiconductor region of the one memory cell is connected to the one writing bit line out of the plural writing bit lines.

15. A thin film memory array comprising:

a plurality of word lines;

a plurality of bit lines that are insulated from and intersect the word lines;

a plurality of common lines; and

a plurality of memory cells according to claim 12,

wherein, in a portion where one of the plural word lines and one of the plural bit lines intersect one another, the first and second conductive gates of one of the plural memory cells are connected to the one word line out of the plural word lines,

wherein the first semiconductor region and the third semiconductor region of the one memory cell is connected to the one bit line out of the plural bit lines, and

wherein the second semiconductor region of the one memory cell is connected to one of the plural common lines.

16. A thin film memory array comprising:

a plurality of word lines;

a plurality of bit lines that are insulated from and intersect the word lines;

a plurality of common lines; and

a plurality of memory cells according to claim 12,

wherein, in a portion where one of the plural word lines and one of the plural bit lines intersect one another, the first conductive gate of one of the plural memory cells is connected to the one word line out of the plural word lines,

wherein the first semiconductor region and the third semiconductor region of the one memory cell is connected to the one bit line out of the plural bit lines, and

wherein the second semiconductor region of the one memory cell is connected to one of the plural common lines.

17. A thin film memory array according to claim 15,

wherein the first conductive gate and the second conductive gate are continuous throughout one cell and are continued further to extend between cells adjacent in the word direction to form a part of a word line, and

wherein the first channel formation semiconductor thin film portion or the second channel formation semiconductor thin film portion in one cell is separated from that of its adjacent cell.

18. A thin film memory array according to claim 16,

wherein the first conductive gate is extended to be continuous between cells adjacent in the word direction and forms a part of a word line, and

wherein the first channel formation semiconductor thin film portion or the second channel formation semiconductor thin film portion in one cell is separated from that of its adjacent cell.

19. A thin film memory array according to claim 16, wherein a part of the common lines is formed from a continuous second semiconductor region stretching over adjacent cells.

20. A thin film memory array according to claim 18,

wherein cells are arranged such that the first semiconductor regions and the second semiconductor regions of adjacent cells form a mirror image relation to build an array, and

wherein the first and, third semiconductor regions are continued from a cell to its adjacent cell in one direction whereas the second semiconductor region is continued from a cell to its adjacent cell in the other direction.

21. A thin film memory array according to claim 16,

wherein the semiconductor thin film is continuous in the word line direction, and

wherein the first semiconductor region of one cell is electrically insulated from the first semiconductor region of its adjacent cell by the third semiconductor region.

22. A writing method to be applied to a thin film memory cell of claim 12,

wherein a value obtained by subtracting the electric potential of the third semiconductor region from the electric potential of the second conductive gate is set to a level exceeding a gate threshold voltage V_{th2r} of a channel that is placed in the second channel formation semiconductor thin film portion to deliver opposite conductivity type carriers from the third semiconductor region which is viewed from the second conductive gate, and

wherein, by setting the electric potential difference between the second conductive gate and the third semiconductor region as above, carriers of the opposite conductivity type are implanted from the third semiconductor region through the second channel formation semiconductor thin film portion into the first channel formation semiconductor thin film portion, so that the gate threshold voltage of a first conductivity type channel in the first channel formation semiconductor thin film portion which is viewed from the first conductive gate is changed to a first value.

23. A writing method to be applied to a thin film memory cell of claim 12,

wherein a value obtained by subtracting the electric potential of the third semiconductor region from the electric potential of the second conductive gate is set to a level exceeding a gate threshold voltage V_{th2r} of a channel that is placed in the second channel formation semiconductor thin film portion to deliver opposite conductivity type carriers from the third semiconductor region which is viewed from the second conductive gate, and

wherein, by setting the electric potential difference between the second conductive gate and the third semiconductor region as above, carriers of the opposite conductivity type are implanted from the third semiconductor region through the second channel formation semiconductor thin film portion into the first channel formation semiconductor thin film portion, so that the gate threshold voltage of a first conductivity type channel in the first channel formation semiconductor thin film portion which is viewed from the first conductive gate is changed to a first value.

24. A writing method to be applied to a thin film memory cell of claim 12,

wherein a value obtained by subtracting the electric potential of the third semiconductor region from the electric potential of the second conductive gate is set to a level sufficiently exceeding a gate threshold voltage of a channel that is placed in the second channel formation semiconductor thin film portion to deliver opposite conductivity type carriers from the third semiconductor region which is viewed from the second conductive gate, and the electric potential of the third semiconductor region with respect to the same gate electric potential is set to multilevel, so that the first value of the gate threshold voltage has multilevel.

25. An erasing method to be applied to a thin film memory cell of claim 12,

wherein a value obtained by subtracting, from the electric potential of the second conductive gate, the electric potential of the opposite conductivity type carriers implanted into the first channel formation semiconductor

thin film portion is set to a level exceeding a gate threshold voltage of an opposite conductivity type channel in the second channel formation semiconductor thin film portion which is viewed from the second conductive gate, and

wherein, by setting the electric potential difference as above, carriers of the opposite conductivity type are drawn from the first channel formation semiconductor thin film portion into the third semiconductor region, so that the gate threshold voltage of a first conductivity type channel in the first channel formation semiconductor thin film portion which is viewed from the first conductive gate is changed to a second value.

26. An erasing method to be applied to a thin film memory cell of claim 12,

wherein a value obtained by subtracting, from the electric potential of the first conductive gate, the electric potential of the opposite conductivity type carriers implanted into the first channel formation semiconductor thin film portion is set to a level exceeding a gate threshold voltage of an opposite conductivity type channel in the second channel formation semiconductor thin film portion which is viewed from the first conductive gate, and

wherein, by setting the electric potential difference as above, carriers of the opposite conductivity type are drawn from the first channel formation semiconductor thin film portion into the third semiconductor region, so that the gate threshold voltage of a first conductivity type channel in the first channel formation semiconductor thin film portion which is viewed from the first conductive gate is changed to a second value.

27. An erasing method to be applied to a thin film memory cell of claim 12, wherein an electric potential is given in the direction that draws carriers of the opposite conductivity type to the first semiconductor region.

28. An erasing method to be applied to a thin film memory cell of claim 12, wherein an electric potential is given in the direction that draws carriers of the opposite conductivity type to the second semiconductor region.

29. An operation method to be applied to a thin film memory cell of claim 12,

wherein a value obtained by subtracting the electric potential of the third semiconductor region from the electric potential of the second conductive gate is set to a level exceeding a gate threshold voltage of a channel that is placed in the second channel formation semiconductor thin film portion to deliver opposite conductivity type carriers from the third semiconductor region which is viewed from the second conductive gate,

wherein a first gate threshold voltage is written when the electric potential of the third semiconductor region is biased forward with respect to the electric potential of the second semiconductor region, and

wherein a second gate threshold voltage is written when the electric potential of the third semiconductor region is zero-biased or biased backward with respect to the same second gate voltage.

30. An operation method to be applied to a thin film memory cell of claim 12,

wherein a value obtained by subtracting the electric potential of the third semiconductor region from the

electric potential of the first conductive gate is set to a level exceeding a gate threshold voltage of a channel that is placed in the second channel formation semiconductor thin film portion to deliver opposite conductivity type carriers from the third semiconductor region which is viewed from the first conductive gate,

wherein a first gate threshold voltage is written when the electric potential of the third semiconductor region is biased forward with respect to the electric potential of the second semiconductor region, and

wherein a second gate threshold voltage is written when the electric potential of the third semiconductor region is zero-biased or biased backward with respect to the same first gate voltage.

31. A reading method to be applied to a thin film memory cell of claim 12, wherein the voltage of the first conductive gate with respect to the second semiconductor region is set to a prescribed value that exceeds one or both of a first gate threshold voltage and a second gate threshold voltage and whether a current flowing between the first semiconductor region and the second semiconductor region is large or small is detected to judge stored information.

32. A reading method according to claim 31, wherein a voltage applied between the first and second semiconductor regions does not exceed a value equal to or larger than the energy gap of the semiconductor thin film which is converted into voltage.

33. An operation method to be applied to a thin film memory array of claim 14,

wherein, during writing, the word line electric potential is obtained by subtracting 0.4 V (± 0.1 V) from the common line electric potential, a writing bit line electric potential is obtained by adding 0.2 V (± 0.1 V) to the common electric potential, and a reading bit line electric potential is the common electric potential,

wherein, during erasing, the word line electric potential is obtained by subtracting 0.5V (± 0.1 V) from the com-

mon line electric potential, a writing bit line electric potential is the common electric potential, and a reading bit line electric potential is the common electric potential, and

wherein, during reading, the word line electric potential is obtained by adding 0.7 V (± 0.1 V) to the common line electric potential, a writing bit line electric potential is the common electric potential, and the reading bit line electric potential is obtained by adding 0.3 V (± 0.1 V) to the common electric potential.

34. An operation method to be applied to a thin film memory array of claim 16,

wherein, during writing, the word line electric potential is obtained by subtracting 0.3 V (± 0.1 V) from the common line electric potential, "1" writing bit line electric potential is obtained by adding 0.3 V (± 0.1 V) to the common electric potential, and "0" writing bit line electric potential is obtained by subtracting 0.3 V (± 0.1 V) from the common electric potential, and

wherein, during reading, the word line electric potential is obtained by adding 0.7 V (± 0.1 V) to the common line electric potential and the bit line electric potential is obtained by adding 0.2 V (± 0.1 V) to the common electric potential.

35. A method of manufacturing a thin film memory array of claim 16, comprising:

forming a third semiconductor region through selective crystal growth;

oxidizing at least a side face of the third semiconductor region that has been formed by selective crystal growth; and

forming a first semiconductor region through selective epitaxial growth.

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